One Watt Darlington Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	MPSW45 MPSW45A	V _{CES}	40 50	Vdc
Collector - Base Voltage	MPSW45 MPSW45A	V _{CBO}	50 60	Vdc
Emitter - Base Voltage	V _{EBO}	12	Vdc	
Collector Current – Continuo	Ic	1.0	Adc	
Total Device Dissipation @ 7 Derate above 25°C	P _D	1.0 8.0	W mW/°C	
Total Device Dissipation @ 7 Derate above 25°C	P _D	2.5 20	W mW/°C	
Operating and Storage Junc Temperature Range	tion	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

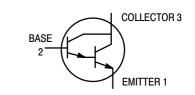
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

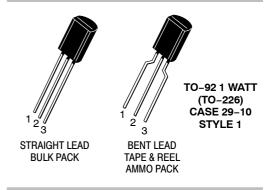
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



MPSW45x = Device Code

x = 45A Devices

A = Assembly Location

Y = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, V_{BE} = 0$)	MPSW45 MPSW45A	V _{(BR)CES}	40 50	- -	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	MPSW45 MPSW45A	V _{(BR)CBO}	50 60		Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	12	-	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$	MPSW45 MPSW45A	I _{CBO}	- -	100 100	nAdc
Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)		I _{EBO}	_	100	nAdc
ON CHARACTERISTICS (Note 1)			•		
DC Current Gain $ \begin{array}{l} (I_{C}=200 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc)} \\ (I_{C}=500 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc)} \\ (I_{C}=1.0 \text{ Adc, V}_{CE}=5.0 \text{ Vdc)} \end{array} $		h _{FE}	25,000 15,000 4,000	150,000 - -	-
Collector – Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 2.0 mAdc)		V _{CE(sat)}	-	1.5	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 2.0 mAdc)		V _{BE(sat)}	-	2.0	Vdc
Base – Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product (I _C = 200 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	-	MHz
Collector–Base Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{cb}	-	6.0	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.

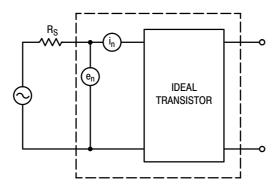


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

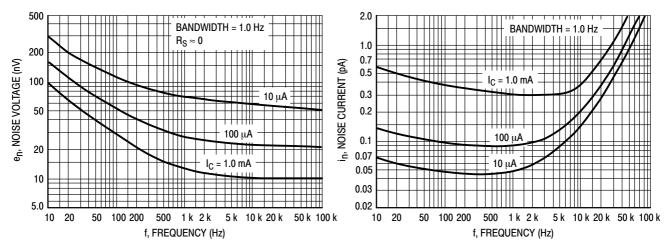


Figure 2. Noise Voltage

Figure 3. Noise Current

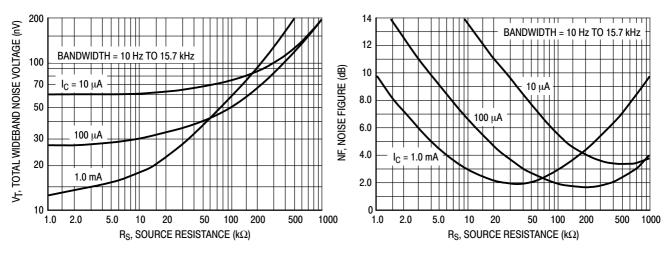


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

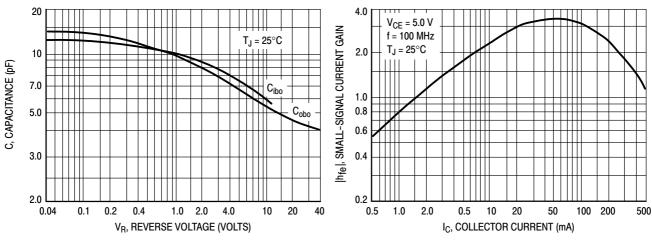


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

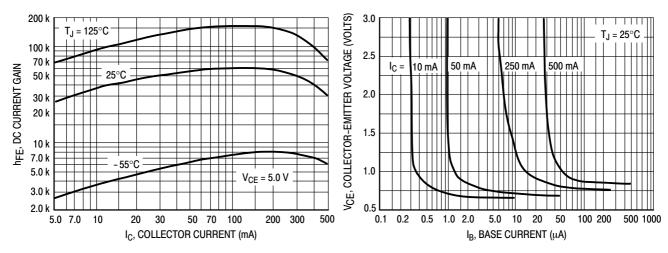


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

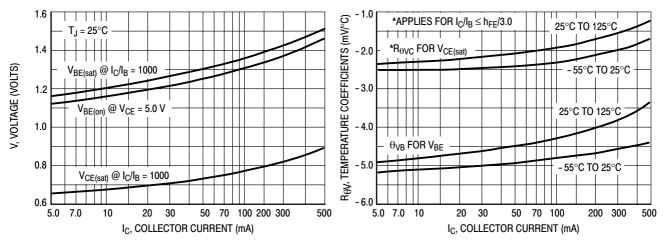


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

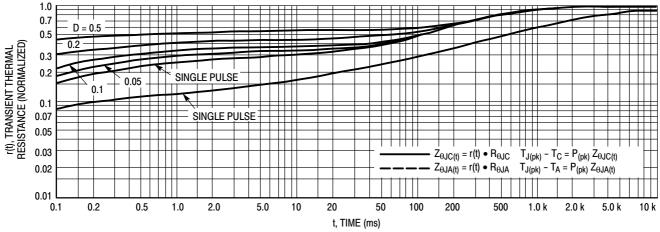
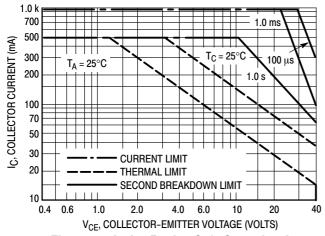


Figure 12. Thermal Response



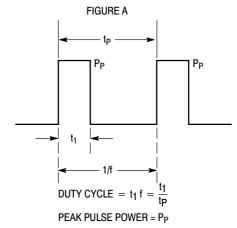


Figure 13. Active Region Safe Operating Area

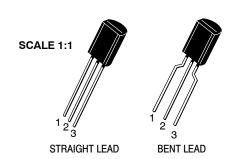
Design Note: Use of Transient Thermal Resistance Data

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW45G	TO-92 (Pb-Free)	5,000 Units / Box
MPSW45RLREG	TO-92 (Pb-Free)	2,000 / Tape & Reel
MPSW45A	TO-92	5,000 Units / Box
MPSW45AG	TO-92 (Pb-Free)	5,000 Units / Box
MPSW45ARLRA	TO-92	2,000 / Tape & Reel
MPSW45ARLRAG	TO-92 (Pb-Free)	2,000 / Tape & Reel
MPSW45AZL1	TO-92	2,000 / Ammo Pack
MPSW45AZL1G	TO-92 (Pb-Free)	2,000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

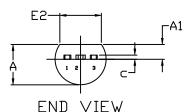


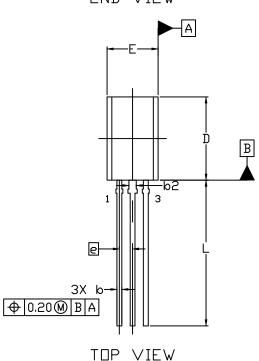


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DATE 05 MAR 2021

STRAIGHT LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

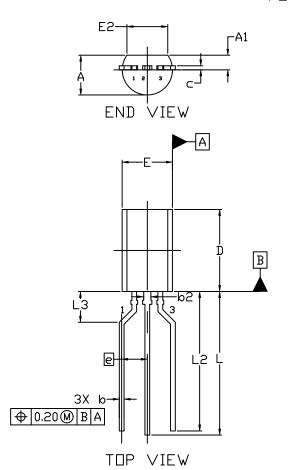
	MILLIMETERS						
DIM	MIN.	N□M.	MAX.				
Δ	3.75	3.90	4.05				
A1	1.28	1.43	1.58				
Ø	0.38	0.465	0.55				
ρQ	0.62	0.70	0.78				
C	0.35	0.40	0.45				
D	7.85	8.00	8.15				
E	4.75	4.90	5.05				
E2	3.90						
е	1.27 BSC						
L	13.80	14.00	14.20				

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NOTES:

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	MILLIMETERS						
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c	0.35	0.40	0.45				
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Ε	4.75	4.90	5.05				
E2	3.90						
e		2.50 BSC					
L	13.80	14.00	14.20				
L2	13.20	13.60	14.00				
L3	3.00 REF						

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CASE 29-10 ISSUE D

DATE 05 MAR 2021

2.	EMITTER BASE COLLECTOR		BASE EMITTER COLLECTOR		ANODE ANODE CATHODE		CATHODE CATHODE ANODE		DRAIN SOURCE GATE
	GATE	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN	STYLE 8: PIN 1. 2. 3.	DRAIN GATE	2.	BASE 1	2.	CATHODE GATE ANODE
2.	ANODE CATHODE & ANODE	PIN 1. 2.	MAIN TERMINAL 1	PIN 1. 2.	ANODE 1 GATE	2.	EMITTER	2.	ANODE 1 CATHODE ANODE 2
2.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER		ANODE CATHODE NOT CONNECTED		GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.		2.	SOURCE GATE DRAIN		GATE SOURCE DRAIN	PIN 1. 2.	EMITTER	2.	MT 1
	V _{CC}			PIN 1. 2.		PIN 1. 2.	NOT CONNECTED ANODE CATHODE		
	GATE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	2.	RETURN INPUT OUTPUT	PIN 1. 2.	INPUT GROUND LOGIC		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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